Discrete POWER & Signal **Technologies**

MPSW06

MPSW06

FAIRCHILD

SEMICONDUCTOR IM



NPN General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 33. See MPSA06 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Characteristic	Мах	Units
		MPSW06	
PD	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

TA = 25°C unless otherwise noted

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

NPN General Purpose Ampl (cont

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	ical Characteristics TA:	= 25°C unless otherwise noted			
Symbol	Parameter	Test Conditions	Min	Мах	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 1.0$ mA, $I_{\rm B} = 0$	80		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$	4.0		V
I _{CEO}	Collector-Cutoff Current	$V_{CE} = 60 \text{ V}, \text{ I}_{B} = 0$		0.1	μA
Сво	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_E = 0$		0.1	μA
				•	
	ACTERISTICS DC Current Gain	$I_{C} = 10$ mA, $V_{CE} = 1.0$ V $I_{C} = 100$ mA, $V_{CF} = 1.0$ V	100 100		
η _{FE}		$I_{c} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{c} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{c} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$		0.25	V
ON CHAF h _{FE} V _{CE(sat)} V _{BE(on)}	DC Current Gain	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$		0.25	V V V
h _{FE} V _{CE(sat)} V _{BE(on)}	DC Current Gain Collector-Emitter Saturation Voltage	$I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$			

*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

Spice Model

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NPN (ls=8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.16K Ne=1.368 lse=73.27f lkf=.1096 Xtb=1.5 Br=11.1 Nc=2 lsc=0 lkr=0 Rc=.25 Cjc=18.36p Mjc=.3843 Vjc=.75 Fc=.5 Cje=55.61p Mje=.3834 Vje=.75 Tr=72.15n Tf=516.1p ltf=.5 Vtf=4 Xtf=6 Rb=10)